



BAV74

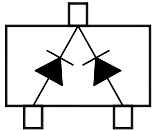
Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time

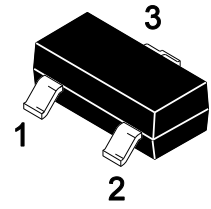
Pin Configuration

3.Cathode1、 Cathode2



1.Anode1 2.Anode2

Package



1.Anode1 2.Anode2
3.Cathode1、 Cathode2

Marking Code : A4

Electrical Characteristics (at $T_J = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	60	V
Reverse Voltage	V_R	50	V
Average Rectified Forward Current	$I_{F(AV)}$	Single Diode Loaded 215	mA
		Double Diode Loaded 125	
Maximum Peak Forward Current	I_{FM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$	0.5
		at $t = 1\text{ ms}$	1
		at $t = 1\text{ }\mu\text{s}$	4
Power Dissipation	P_D	350	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$



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9`YWF]WU`7\ UFUWHf]gh]Wg`fH₅1&) °CŁ

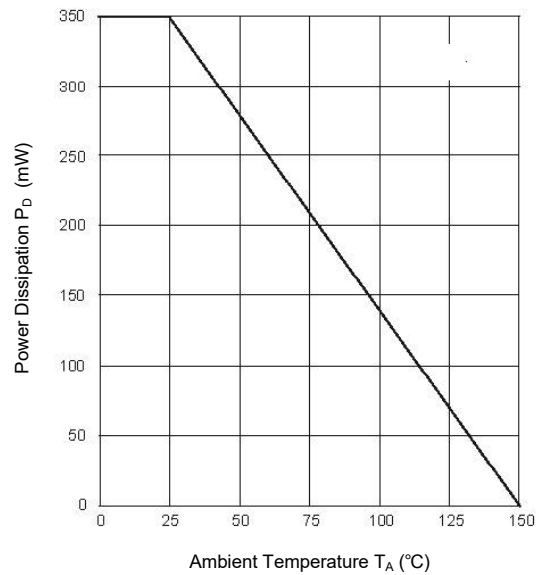
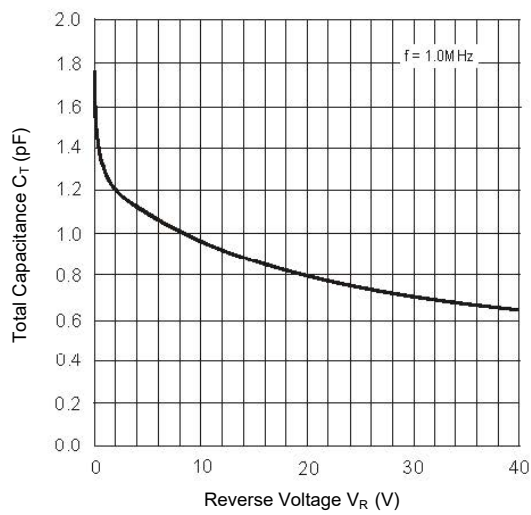
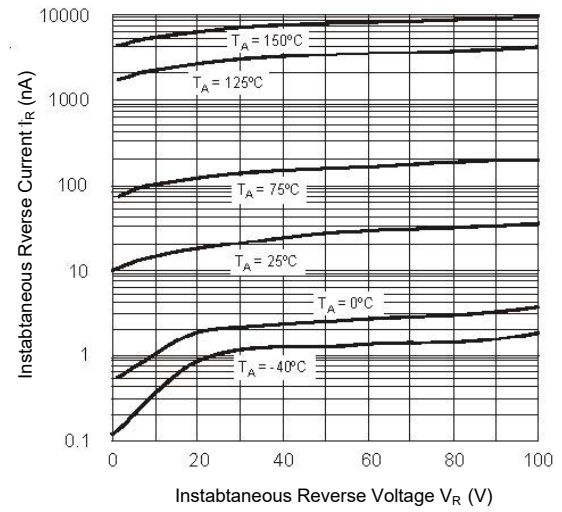
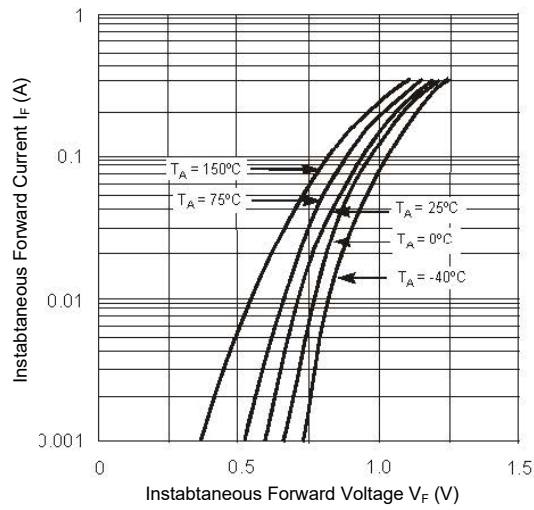
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1$ mA at $I_F = 10$ mA at $I_F = 50$ mA at $I_F = 150$ mA	V_F	--	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 25$ V at $V_R = 50$ V at $V_R = 25$ V, at $T_J = 150$ °C at $V_R = 50$ V, at $T_J = 150$ °C	I_R	--	0.03 0.1 30 100	μ A
Typical Junction Capacitance at $V_R = 0$ V, $f = 1$ MHz	C_j	--	2	pF
Maximum Reverse Recovery Time at $I_F = 10$ mA, $V_R = 6$ V, $I_{RR} = 1$ mA, $R_L = 100$ Ω	T_{rr}	--	4	nS



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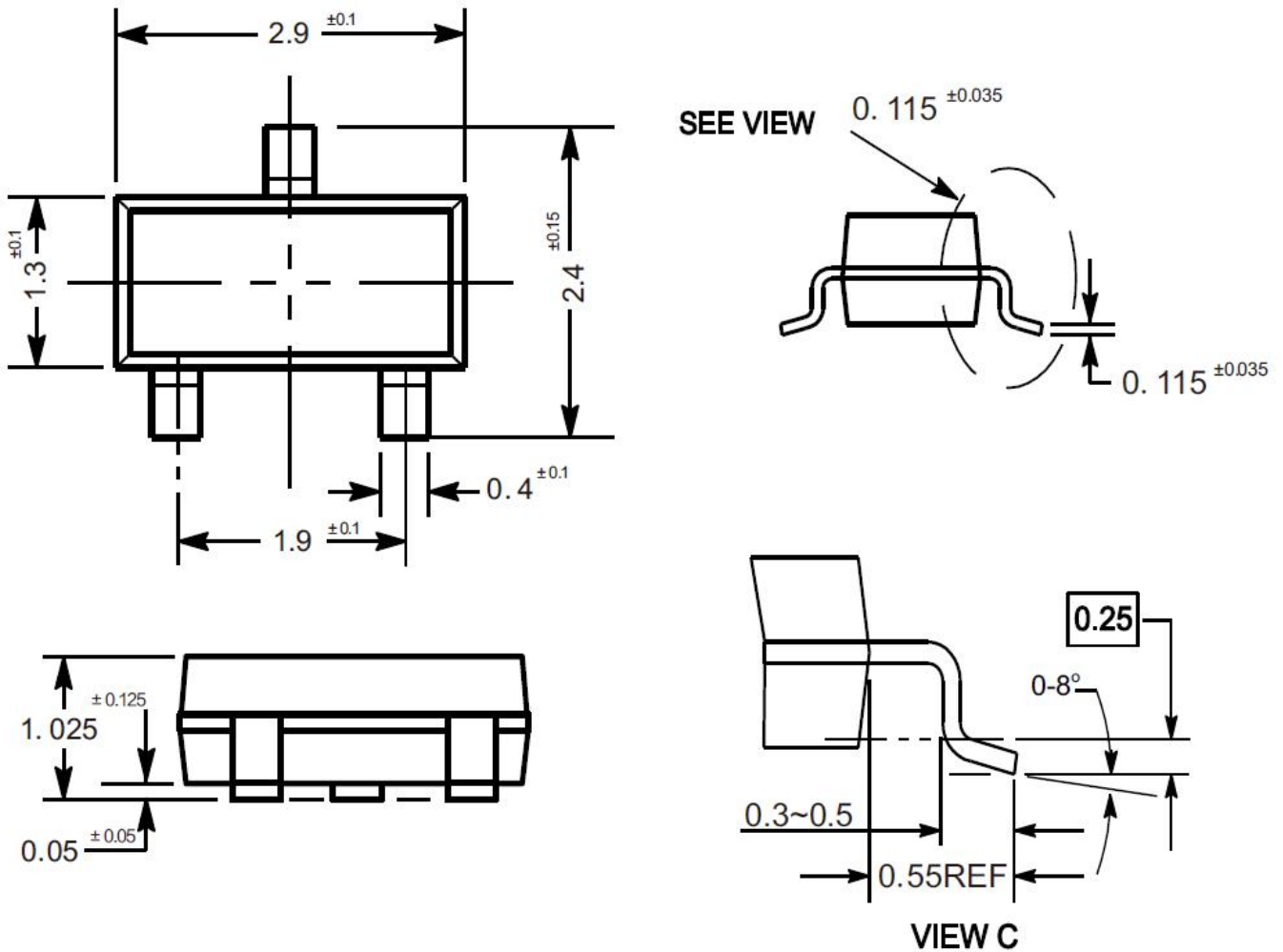
Typical Characteristic Curves



Package Outline

SOT-23

Dimensions in mm



Ordering Information

Device	Package	Shipping
BAV74	SOT-23	3,000PCS/Reel&7inches